Schottky-Barrier Diodes (SBD)

1 in one-package

Device type	SMD	Maximum rating V_{RRM} Volts	$I_{F(AV)}$ *1 Amps.	I_{FSM}*2 Amps.	Thermal rating Tj and Tstg ˚C	Characteristics(Ta=25˚C) V_{FM} Max. Volts	I_{RRM}*3 Max.mA	Rth(j-c) ˚C/W	Package	Net mass Grams
ERA82-004		40	0.6(Ta=60˚C)	25	-40 to +150	0.55(I_F=0.6A)	1		Lead-1	0.18
SC802-04	SMD	40	1.0(Tl=115˚C) *5	40	-40 to +150	0.55(I_F=1.0A)	2		SC	0.06
SC802-06	SMD	60	1.0(Tl=111˚C) *5	30	-40 to +150	0.58(I_F=1.0A)	2		SC	0.06
SC802-09	SMD	90	1.0(Tl=110˚C) *5	30	-40 to +150	0.85(I_F=1.0A)	2		SC	0.06
ERA83-004		40	1.0(Tl=115˚C)	50	-40 to +150	0.55(I_F=1.0A)	2		Lead-1	0.18
ERA83-006		60	1.0(Tl=111˚C)	30	-40 to +150	0.58(I_F=1.0A)	2		Lead-1	0.18
ERA81-004		40	1.0(Ta=25˚C)	50	-40 to +150	0.55(I_F=1.0A)	2		Lead-2	0.22
ERA84-009		90	1.0(Ta=25˚C) *6	30	-40 to +150	0.9 (I_F=1.0A)	1		Lead-2	0.22
ERA85-009		90	1.0(Tl=110˚C)	30	-40 to +150	0.82(I_F=1.0A)	1		Lead-1	0.18
CB803-03		30	2.0(Tl=133˚C)	80	-40 to +150	0.47(I_F=1.5A)	5		Lead-3	0.3
ERB83-004		40	2.0(Tl=130˚C)	100	-40 to +150	0.55(I_F=2.0A)	5		Lead-3	0.3
ERB83-006		60	2.0(Tl=104˚C)	60	-40 to +150	0.58(I_F=2.0A)	5		Lead-3	0.3
ERB81-004		40	2.0(Tl=130˚C)	100	-40 to +150	0.55(I_F=2.0A)	5		Lead-4	0.5
ERB84-009		90	2.0(Ta=25˚C) *7	60	-40 to +150	0.9 (I_F=2.0A)	2		Lead-4	0.5
ED807-03		30	3.0(Tl=134˚C)	120	-40 to +150	0.47(I_F=3.0A)	5		Lead-7	1.2
ERC81-004		40	3.0(Tl=130˚C)	120	-40 to +150	0.55(I_F=3.0A)	5		Lead-7	1.2
ERC81-006		60	3.0(Tl=104˚C)	80	-40 to +150	0.58(I_F=3.0A)	5		Lead-7	1.2
ERC84-009		90	3.0(Tl=85˚C)	120	-40 to +150	0.8 (I_F=3.0A)	5		Lead-7	1.2
ERC81S-004		40	5.0(Tl=25˚C)	120	-40 to +150	0.55 (I_F=5.0A)	5		Lead-7	1.2
KS826S04	SMD	40	5.0(Tc=92˚C)	80	-40 to +150	0.55(I_F=5.0A)	5	10	K-pack(S)	0.6
ERC80-004		40	5.0(Tc=102˚C)	120	-40 to +150	0.55(I_F=5.0A)	5	5.0	TO-220AB	2.0
YG811S04R		40	5.0(Tc=102˚C)	120	-40 to +150	0.55(I_F=5.0A)	5	5.0	TO-220F15	2.3
YG811S06R		60	5.0(Tc=100˚C)	80	-40 to +150	0.59(I_F=5.0A)	5	5.0	TO-220F15	2.3
YG811S09R		90	5.0(Tc=85˚C)	80	-40 to +150	0.9 (I_F=4.0A)	5	5.0	TO-220F15	2.3
ERC62-004		45	10 (Tc=110˚C)	250	-40 to +150	0.6 (I_F=10A)	2	2.0	TO-220AB	2.0
ERC62M-004		45	10 (Tc=101˚C)	250	-40 to +150	0.6 (I_F=10A)	2	2.5	TO-220F17	2.3
ERD80-004		40	15 (Tc=100˚C)	250	-40 to +150	0.55(I_F=12.5A)	10	2.0	TO-3P	5.5
ERD81-004		40	15 (Tc=100˚C)	250	-40 to +125	0.55(I_F=15A)	100*4		Power M5R	5.5
ERE81-004		40	30 (Tc=100˚C)	600	-40 to +125	0.55(I_F=30A)	200*4		Power M6R	12
ERG81-004		40	60 (Tc=90˚C)	850	-40 to +125	0.55(I_F=50A)	300*4		Power M8R	25
ERG81A-004		40	60 (Tc=90˚C)	850	-40 to +125	0.55(I_F=50A)	300*4		Power M8R	25

( ) Conditions
*1 Resistive load *2 Sine wave, 10ms *3 V_R=V_{RRM}
*4 Tj=125˚C
*5 Mounted to fabric base epoxy resin printed circuits (land 15 x 15mm)
*6 P.C boad mounting (land 10 x 10mm)
*7 Mounted Cu fins (20 x 20mm) on the both leads

Letter symbols

V_{RRM}	Repetitive peak reverse voltage	T_{stg}	Storage temperature
V_{RSM}	Non-repetitive peak reverse voltage	V_{FM}	Forward voltage
I_O	Average output current	I_{RRM}	Reverse current
I_{FSM}	Surge current	t_{rr}	Reverse recovery time
T_j	Junction temperature	R_{thj-c}	Thermal resistance (Junction to case)
T_a	Ambient temperature	T_l	Lead temperature
T_c	Case temperature	$I_{F(AV)}$	Average forward current

Schottky-Barrier Diodes (SBD)

2 in one-package

Device type	SMD	Maximum rating VRRM Volts	Io *1 Amps.	IFSM*2 Amps.	Thermal rating Tj and Tstg ˚C	Characteristics(Ta=25˚C) VFM Max. Volts	IRRM*3 Max.mA	Rth(j-c) ˚C/W	Package	Net mass Grams
KS823C03	SMD	30	5.0(Tc=87˚C)	60	-40 to +150	0.47(IF=2.5A)	5.0	10	K-pack(S)	0.6
KS823C04	SMD	40	5.0(Tc=87˚C)	60	-40 to +150	0.55(IF=2.5A)	5.0	10	K-pack(S)	0.6
KP823C03		30	5.0(Tc=87˚C)	60	-40 to +150	0.47(IF=2.5A)	5.0	10	K-pack(P)	0.6
KP823C04		40	5.0(Tc=87˚C)	60	-40 to +150	0.55(IF=2.5A)	5.0	10	K-pack(P)	0.6
TP801C04		40	5.0(Tc=103˚C)	100	-40 to +150	0.55(IF=2.0A)	5.0	5.0	T-pack(P)	1.6
TP801C06		60	5.0(Tc=103˚C)	60	-40 to +150	0.58(IF=2.0A)	5.0	5.0	T-pack(P)	1.6
ESAB82-004		40	5.0(Tc=103˚C)	100	-40 to +150	0.55(IF=2.0A)	5.0	5.0	TO-220AB	2.0
YG801C04R		40	5.0(Tc=103˚C)	100	-40 to +150	0.55(IF=2.0A)	5.0	5.0	TO-220F15	2.3
YG801C06R		60	5.0(Tc=103˚C)	60	-40 to +150	0.58(IF=2.0A)	5.0	5.0	TO-220F15	2.3
YG801C09R		90	5.0(Tc=95˚C)	60	-40 to +150	0.9 (IF=2.0A)	2.0	5.0	TO-220F15	2.3
YG801C10R		100	5.0(Tc=117˚C)	60	-40 to +150	0.8 (IF=1.5A)	0.7	2.5	TO-220F15	2.3
ESAB85-009		90	5.0(Tc=95˚C)	60	-40 to +150	0.9 (IF=2.0A)	2.0	5.0	TO-220AB	2.0
YG831C03R		30	6.0(Tc=127˚C)	90	-40 to +150	0.45(IF=2.0A)	5.0	5.0	TO-220F15	2.3
YG831C04R		40	6.0(Tc=122˚C)	80	-40 to +150	0.53(IF=2.0A)	2.0	5.0	TO-220F15	2.3
KS883C02	SMD	20	7.0(Tc=89˚C)	60	-40 to +150	0.39(IF=2.5A)	10.0	10.0	K-pack (S)	0.6
KP883C02		20	7.0(Tc=89˚C)	60	-40 to +150	0.39(IF=2.5A)	10.0	10.0	K-pack (P)	0.6
YG881C02R		20	8.0(Tc=102˚C)	80	-40 to +150	0.39(IF=2.0A)	10.0	5.0	TO-220F15	2.3
TS802C04	SMD	40	10 (Tc=97˚C)	120	-40 to +150	0.55(IF=4.0A)	5.0	3.0	T-pack(S)	1.6
TS802C06	SMD	60	10 (Tc=96˚C)	80	-40 to +150	0.58(IF=4.0A)	5.0	3.0	T-pack(S)	1.6
TS802C09	SMD	90	10 (Tc=92˚C)	80	-40 to +150	0.9 (IF=4.0A)	5.0	3.0	T-pack(S)	1.6
TP802C04		40	10 (Tc=97˚C)	120	-40 to +150	0.55(IF=4.0A)	5.0	3.0	T-pack(P)	1.6
TP802C06		60	10 (Tc=96˚C)	80	-40 to +150	0.58(IF=4.0A)	5.0	3.0	T-pack(P)	1.6
TP802C09		90	10 (Tc=92˚C)	80	-40 to +150	0.9 (IF=4.0A)	5.0	3.0	T-pack(P)	1.6
ESAC82-004		40	10 (Tc=97˚C)	120	-40 to +150	0.55(IF=4.0A)	5.0	3.0	TO-220AB	2.0
YG802C03R		30	10 (Tc=102˚C)	120	-40 to +150	0.47(IF=4.0A)	5.0	3.5	TO-220F15	2.3
YG802C04R		40	10 (Tc=95˚C)	120	-40 to +150	0.55(IF=4.0A)	5.0	3.5	TO-220F15	2.3
YG802C06R		60	10 (Tc=92˚C)	80	-40 to +150	0.58(IF=4.0A)	5.0	3.5	TO-220F15	2.3
YG802C09R		90	10 (Tc=87˚C)	80	-40 to +150	0.9 (IF=4.0A)	5.0	3.5	TO-220F15	2.3
YG802C10R		100	10 (Tc=102˚C)	80	-40 to +150	0.8 (IF=3.0A)	1.2	2.5	TO-220F15	2.3
ESAC85-009		90	10 (Tc=92˚C)	80	-40 to +150	0.9 (IF=4.0A)	5.0	3.0	TO-220AB	2.0
YG832C03R		30	12 (Tc=118˚C)	120	-40 to +150	0.45 (IF=4.0A)	5.0	3.5	TO-220F15	2.3
YG832C04R		40	12 (Tc=112˚C)	120	-40 to +150	0.53 (IF=4.0A)	3.0	3.5	TO-220F15	2.3
ESAC61-004		40	12 (Tc=100˚C)	120	-40 to +150	0.6 (IF=6.0A)	5.0	2.0	TO-3P	5.5
YG882C02R		20	16 (Tc=93˚C)	120	-40 to +150	0.39 (IF=4.0A)	10	3.5	TO-220F15	2.3
ESAC87-009		90	16 (Tc=90˚C)	100	-40 to +150	0.9 (IF=6.0A)	10	1.5	TO-3P	5.5
ESAC87M-009		90	16 (Tc=90˚C)	100	-40 to +150	0.9 (IF=6.0A)	10	2.0	TO-3PF	6.0

( ) Conditions

*1 Square wave duty 1/2 (Average forward current of centertap full wave connection)

*2 Sine wave, 10ms *3 VR=VRRM

Schottky-Barrier Diodes (SBD)

2 in one-package

Device type	SMD	Maximum rating V_{RRM} Volts	I_O *1 Amps.	I_{FSM}*2 Amps.	Thermal rating Tj and Tstg ˚C	Characteristics(Ta=25˚C) V_{FM} Max. Volts	I_{RRM}*3 Max.mA	Rth(j-c) ˚C/W	Package	Net mass Grams
TS805C04	SMD	40	20 (Tc=92˚C)	120	-40 to +150	0.6 (I_F=10A)	15	2.0	T-pack(S)	1.6
TS805C06	SMD	60	20 (Tc=118˚C)	80	-40 to +150	0.58(I_F=8.0A)	15	2.0	T-pack(S)	1.6
TP805C04		40	20 (Tc=92˚C)	120	-40 to +150	0.6 (I_F=10A)	15	2.0	T-pack(P)	1.6
ESAC83-004		40	20 (Tc=95˚C)	120	-40 to +150	0.55(I_F=8.0A)	15	1.5	TO-3P	5.5
ESAC83M-004		40	20 (Tc=79˚C)	120	-40 to +150	0.55(I_F=8.0A)	15	2.5	TO-3PF	6.0
ESAC83M-006		60	20 (Tc=78˚C)	120	-40 to +150	0.58(I_F=8.0A)	15	2.5	TO-3PF	6.0
YG805C04R		40	20 (Tc=83˚C)	120	-40 to +150	0.6 (I_F=10A)	15	2.5	TO-220F15	2.3
YG805C06R		60	20 (Tc=108˚C)	80	-40 to +150	0.58(I_F=8.0A)	15	2.5	TO-220F15	2.3
YG805C10R		100	20 (Tc=91˚C)	100	-40 to +150	0.8 (I_F=5.0A)	2.5	2.5	TO-220F15	2.3
ESAC63-004		45	20 (Tc=92˚C)	120	-40 to +150	0.6 (I_F=10A)	15	2.0	TO-220AB	2.0
YG835C04R		40	22 (Tc=95˚C)	120	-40 to +150	0.53(I_F=8.0A)	6.0	2.5	TO-220F15	2.3
YG835C03R		30	25 (Tc=99˚C)	120	-40 to +150	0.45(I_F=6.0A)	15	2.5	TO-220F15	2.3
ESAD85-009		90	25 (Tc=90˚C)	150	-40 to +150	0.9 (I_F=10A)	20	1.2	TO-3P	5.5
ESAD85M-009		90	25 (Tc=76˚C)	150	-40 to +150	0.9 (I_F=10A)	20	1.7	TO-3PF	6.0
YG885C02R		20	30 (Tc=80˚C)	120	-40 to +150	0.39(I_F=8.0A)	30	2.5	TO-220F15	2.3
PA886C02		20	30 (Tc=85˚C)	250	-40 to +125	0.4 (I_F=12.5A)	50	1.2	TO-3P	5.5
PA806C03		30	30 (Tc=100˚C)	250	-40 to +150	0.47(I_F=12.5A)	20	1.2	TO-3P	5.5
TS808C04	SMD	40	30 (Tc=93˚C)	250	-40 to +150	0.55(I_F=12.5A)	20	1.2	T-pack(S)	1.6
TS808C06	SMD	60	30 (Tc=88˚C)	200	-40 to +150	0.58(I_F=12.5A)	20	1.2	T-pack(S)	1.6
YG808C10R		100	30 (Tc=80˚C)	180	-40 to +150	0.8 (I_F=10A)	20	2.0	TO-220F15	2.3
ESAD83-004		40	30 (Tc=90˚C)	250	-40 to +150	0.55(I_F=12.5A)	20	1.2	TO-3P	5.5
ESAD83-006		60	30 (Tc=90˚C)	200	-40 to +150	0.58(I_F=12.5A)	20	1.2	TO-3P	5.5
ESAD83M-004		40	30 (Tc=79˚C)	250	-40 to +150	0.55(I_F=12.5A)	20	1.7	TO-3PF	6.0
ESAD83M-006		60	30 (Tc=75˚C)	200	-40 to +150	0.58(I_F=12.5A)	20	1.7	TO-3PF	6.0
ESAE83-004		40	60 (Tc=84˚C)	500	-40 to +150	0.55(I_F=25A)	50	0.75	TO-3P	5.5
ESAE83-006		60	60 (Tc=71˚C)	500	-40 to +150	0.58(I_F=25A)	50	0.75	TO-3P	5.5

( ) Conditions
*1 Square wave duty 1/2 (Average forward current of centertap full wave connection)
*2 Sine wave, 10ms *3 V_R=V_{RRM}